

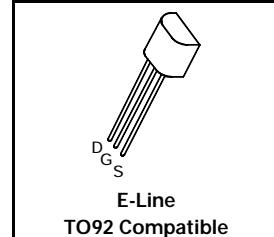
N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

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FEATURES

- * 100 Volt V_{DS}
- * $R_{DS(on)} = 1.5\Omega$
- * Spice model available



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE		UNIT
Drain-Source Voltage	V_{DS}	100		V
Continuous Drain Current at $T_{amb}=25^\circ C$	I_D	450		mA
Pulsed Drain Current	I_{DM}	6		A
Gate-Source Voltage	V_{GS}	± 20		V
Power Dissipation at $T_{amb}=25^\circ C$	P_{tot}	700		mW
Operating and Storage Temperature Range	$T_j \cdot T_{stg}$	-55 to +150		°C

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	100		V	$I_D=1mA, V_{GS}=0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	0.8	2.4	V	$ID=1mA, V_{DS}=V_{GS}$
Gate-Body Leakage	I_{GSS}		100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Zero Gate Voltage Drain Current	I_{DSS}		10 100	μA	$V_{DS}=100V, V_{GS}=0$ $V_{DS}=80V, V_{GS}=0V, T=125^\circ C(2)$
On-State Drain Current(1)	$I_{D(on)}$	2.5		A	$V_{DS}=25V, V_{GS}=10V$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		1.5 1.8	Ω	$V_{GS}=10V, I_D=1.5A$ $V_{GS}=5V, I_D=500mA$
Forward Transconductance(1)(2) g_{fs})		250		mS	$V_{DS}=25V, I_D=1.5A$
Input Capacitance (2)	C_{iss}		100	pF	$V_{DS}=25V, V_{GS}=0V, f=1MHz$
Common Source Output Capacitance (2)	C_{oss}		40	pF	
Reverse Transfer Capacitance (2)	C_{rss}		12	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$		4	ns	$V_{DD}\approx 25V, I_D=1.5A$
Rise Time (2)(3)	t_r		8	ns	
Turn-Off Delay Time (2)(3)	$t_{d(off)}$		20	ns	
Fall Time (2)(3)	t_f		30	ns	

TYPICAL CHARACTERISTICS

